Octal D-type transparent latch (3-State) 74ABT573A

FEATURES

- 74ABT573A is flow-through pinout version of 74ABT373
- Inputs and outputs on opposite side of package allow easy interface to microprocessors
- 3-State output buffers
- Common output enable
- Latch-up protection exceeds 500mA per JEDEC Std 17
- ESD protection exceeds 2000 V per MIL STD 883 Method 3015 and 200 V per Machine Model
- Power-up 3-State
- Power-up reset

DESCRIPTION

The 74ABT573A high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT573A device is an octal transparent latch coupled to eight 3-State output buffers. The two sections of the device are controlled independently by Enable (E) and Output Enable ($\overline{OE}$) control gates. The 74ABT573A is functionally identical to the 74ABT373 but has a flow-through pinout configuration to facilitate PC board layout and allow easy interface with microprocessors.

The data on the D inputs are transferred to the latch outputs when the Latch Enable (E) input is High. The latch remains transparent to the data inputs while E is High, and stores the data that is present one setup time before the High-to-Low enable transition.

The 3-State output buffers are designed to drive heavily loaded 3-State buses, MOS memories, or MOS microprocessors. The active-Low Output Enable ($\overline{OE}$) controls all eight 3-State buffers independent of the latch operation.

When $\overline{OE}$ is Low, the latched or transparent data appears at the outputs. When $\overline{OE}$ is High, the outputs are in the High-impedance "OFF" state, which means they will neither drive nor load the bus.

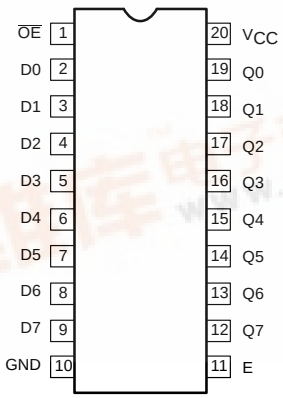
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T_{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t_{PLH} t_{PHL}	Propagation delay Dn to Qn	C_L = 50pF; V_{CC} = 5V	2.8 3.3	ns
C_{IN}	Input capacitance	V_I = 0V or V_{CC}	3	pF
C_{OUT}	Output capacitance	Outputs disabled; V_O = 0V or V_{CC}	6	pF
I_{CCZ}	Total supply current	Outputs disabled; V_{CC} =5.5V	100	µA

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
20-Pin Plastic DIP	–40°C to +85°C	74ABT573A N	74ABT573A N	SOT146-1
20-Pin plastic SO	–40°C to +85°C	74ABT573A D	74ABT573A D	SOT163-1
20-Pin Plastic SSOP Type II	–40°C to +85°C	74ABT573A DB	74ABT573A DB	SOT339-1
20-Pin Plastic TSSOP Type I	–40°C to +85°C	74ABT573A PW	74ABT573APW DH	SOT360-1

PIN CONFIGURATION



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PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1	$\overline{OE}$	Output enable input (active-Low)
2, 3, 4, 5, 6, 7, 8, 9	D0-D7	Data inputs
19, 18, 17, 16, 15, 14, 13, 12	Q0-Q7	Data outputs
11	E	Enable input (active-High)
10	GND	Ground (0V)
20	V_{CC}	Positive supply voltage

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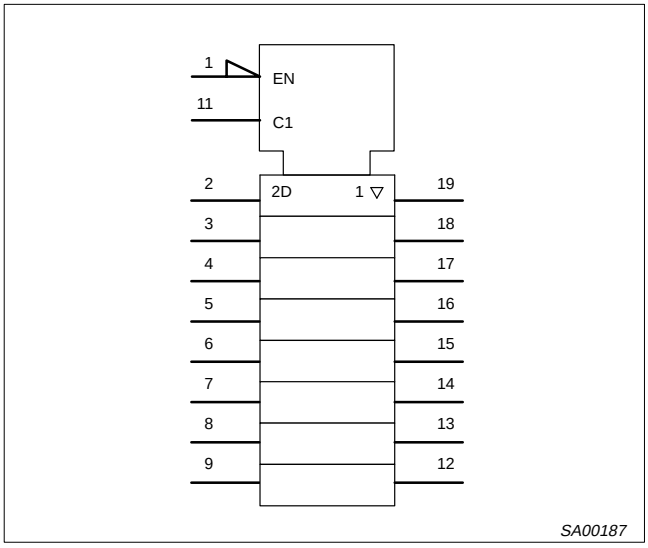
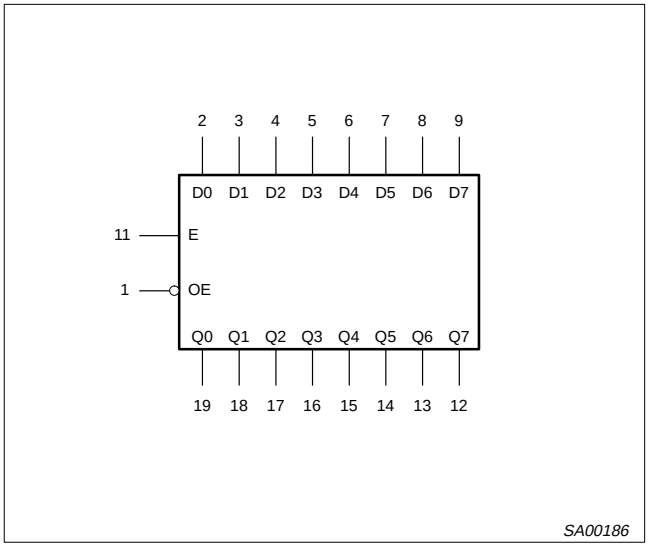
LOGIC SYMBOL (IEEE/IEC)



LOGIC SYMBOL

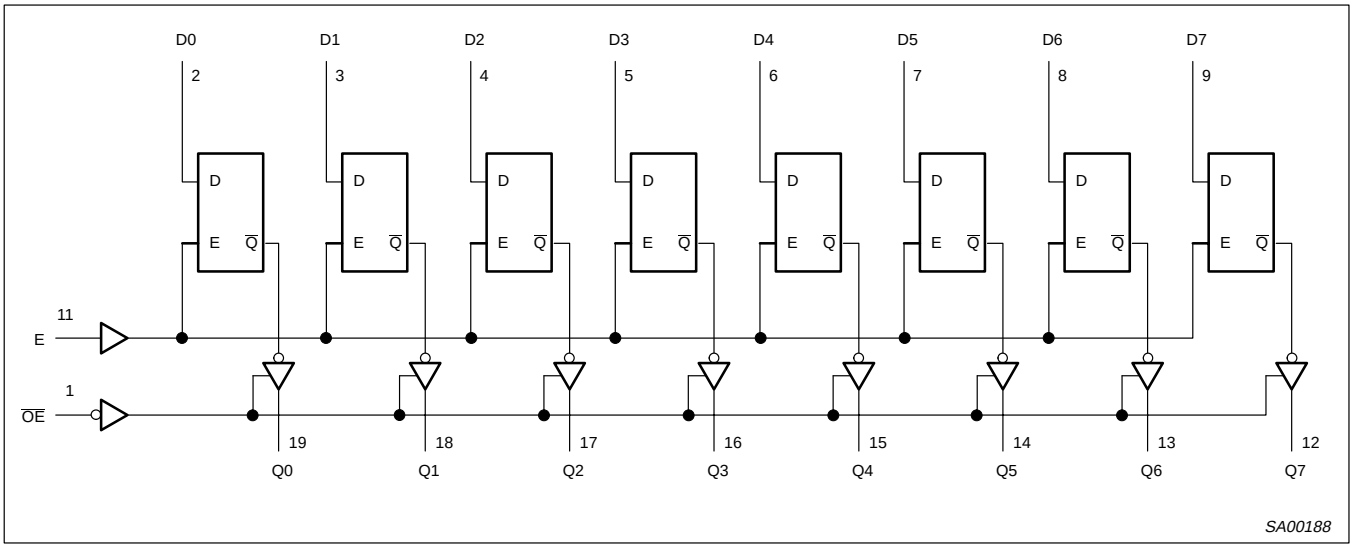


FUNCTION TABLE

INPUTS			INTERNAL	OUTPUTS	OPERATING MODE
$\overline{OE}$	E	Dn	REGISTER	Q0 – Q7	
L L	H H	L H	L H	L H	Enable and read register
L L	↓ ↓	l h	L H	L H	Latch and read register
L	L	X	NC	NC	Hold
H H	L H	X Dn	NC Dn	Z Z	Disable outputs

H = High voltage level
h = High voltage level one set-up time prior to the High-to-Low E transition
L = Low voltage level
l = Low voltage level one set-up time prior to the High-to-Low E transition
NC = No change
X = Don't care
Z = High impedance "off" state
↓ = High-to-Low E transition

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS[1, 2]

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		–0.5 to +7.0	V
I_{IK}	DC input diode current	$V_I < 0$	–18	mA
V_I	DC input voltage[3]		–1.2 to +7.0	V
I_{OK}	DC output diode current	$V_O < 0$	–50	mA
V_{OUT}	DC output voltage[3]	output in Off or High state	–0.5 to +5.5	V
I_{OUT}	DC output current	output in Low state	128	mA
T_{stg}	Storage temperature range		–65 to 150	°C

NOTES:
1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS		UNIT
		Min	Max	
V_{CC}	DC supply voltage	4.5	5.5	V
V_I	Input voltage	0	V_{CC}	V
V_{IH}	High-level input voltage	2.0		V
V_{IL}	Low-level input voltage		0.8	V
I_{OH}	High-level output current		–32	mA
I_{OL}	Low-level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	5	ns/V
T_{amb}	Operating free-air temperature range	–40	+85	°C

DC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			T_{amb} = +25°C			T_{amb} = –40°C to +85°C		
			Min	Typ	Max	Min	Max	
V_{IK}	Input clamp voltage	V_{CC} = 4.5V; I_{IK} = –18mA		–0.9	–1.2		–1.2	V
V_{OH}	High-level output voltage	V_{CC} = 4.5V; I_{OH} = –3mA; V_I = V_{IL} or V_{IH}	2.5	2.9		2.5		V
		V_{CC} = 5.0V; I_{OH} = –3mA; V_I = V_{IL} or V_{IH}	3.0	3.4		3.0		V
		V_{CC} = 4.5V; I_{OH} = –32mA; V_I = V_{IL} or V_{IH}	2.0	2.4		2.0		V
V_{OL}	Low-level output voltage	V_{CC} = 4.5V; I_{OL} = 64mA; V_I = V_{IL} or V_{IH}		0.42	0.55		0.55	V
V_{RST}	Power-up output low voltage[3]	V_{CC} = 5.5V; I_O = 1mA; V_I = GND or V_{CC}		0.13	0.55		0.55	V
I_I	Input leakage current	V_{CC} = 5.5V; V_I = GND or 5.5V		±0.01	±1.0		±1.0	µA
I_{OFF}	Power-off leakage current	V_{CC} = 0.0V; V_O or $V_I \leq$ 4.5V		±5.0	±100		±100	µA
I_{PU}/I_{PD}	Power-up/down 3-State output current[4]	V_{CC} = 2.0V; V_O = 0.5V; $V_{\overline{OE}}$ = Don't Care; V_I = GND or V_{CC}		±5.0	±50		±50	µA
I_{OZH}	3-State output High current	V_{CC} = 5.5V; V_O = 2.7V; V_I = V_{IL} or V_{IH}		5.0	50		50	µA
I_{OZL}	3-State output Low current	V_{CC} = 5.5V; V_O = 0.5V; V_I = V_{IL} or V_{IH}		–5.0	–50		–50	µA
I_{CEX}	Output High leakage current	V_{CC} = 5.5V; V_O = 5.5V; V_I = GND or V_{CC}		5.0	50		50	µA
I_O	Output current[1]	V_{CC} = 5.5V; V_O = 2.5V	–40		–180	–40	–180	mA
I_{CCH}	Quiescent supply current	V_{CC} = 5.5V; Outputs High, V_I = GND or V_{CC}		100	250		250	µA
I_{CCL}		V_{CC} = 5.5V; Outputs Low, V_I = GND or V_{CC}		24	30		30	mA
I_{CCZ}		V_{CC} = 5.5V; Outputs 3-State; V_I = GND or V_{CC}		100	250		250	µA
ΔI_{CC}	Additional supply current per input pin[2]	V_{CC} = 5.5V; one input at 3.4V, other inputs at V_{CC} or GND		0.5	1.5		1.5	mA

NOTES:
1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
2. This is the increase in supply current for each input at 3.4V.
3. For valid test results, data must not be loaded into the flip-flops (or latches) after applying the power.
4. This parameter is valid for any V_{CC} between 0V and 2.1V with a transition time of up to 10msec. For V_{CC} = 2.1V to V_{CC} = 5V ± 10%, a transition time of up to 100µsec is permitted.

AC CHARACTERISTICS

GND = 0V, $t_R = t_F$ = 2.5ns, C_L = 50pF, R_L = 500Ω

SYMBOL	PARAMETER	WAVEFORM	LIMITS					UNIT
			T_{amb} = +25°C V_{CC} = +5.0V			T_{amb} = -40 to +85°C V_{CC} = +5.0V ±0.5V		
			Min	Typ	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation delay Dn to Qn	2	1.5 2.2	2.8 3.3	4.0 4.8	1.5 2.2	4.5 5.3	ns
t_{PLH} t_{PHL}	Propagation delay E to Qn	1	1.2 1.8	2.5 3.0	4.0 4.4	1.2 1.8	4.5 4.7	ns
t_{PZH} t_{PZL}	Output enable time to High and Low level	4 5	1.2 2.7	3.0 3.8	4.5 5.3	1.2 2.7	5.2 5.7	ns
t_{PHZ} t_{PLZ}	Output disable time from High and Low level	4 5	1.5 1.2	2.8 2.2	4.1 3.4	1.5 1.2	4.5 3.8	ns

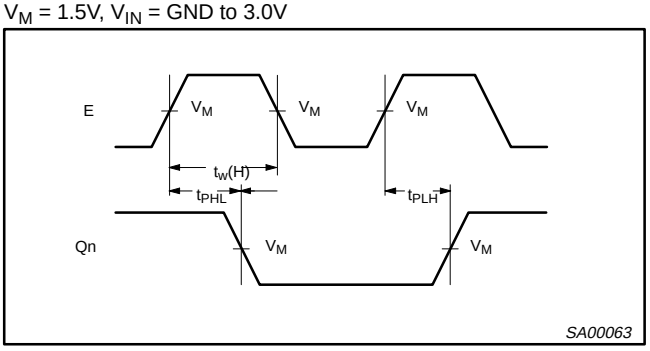
AC SETUP REQUIREMENTS

GND = 0V, $t_R = t_F$ = 2.5ns, C_L = 50pF, R_L = 500Ω

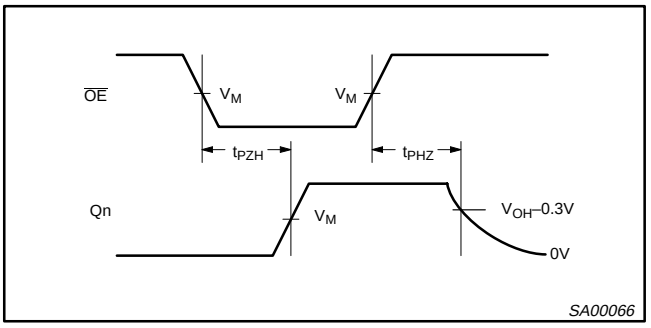
SYMBOL	PARAMETER	WAVEFORM	LIMITS			UNIT
			T_{amb} = +25°C, V_{CC} = +5.0V		T_{amb} = -40 to +85°C, V_{CC} = +5.0V ±0.5V	
			Min	Typ	Min	
$t_s(H)$ $t_s(L)$	Setup time, High or Low Dn to E	3	1.0 1.0	0.3 0.2	1.0 1.0	ns
$t_h(H)$ $t_h(L)$	Hold time, High or Low Dn to E	3	1.0 1.0	–0.1 –0.2	1.0 1.0	ns
$t_w(H)$	E pulse width High	1	2.0	0.7	2.0	ns

AC WAVEFORMS

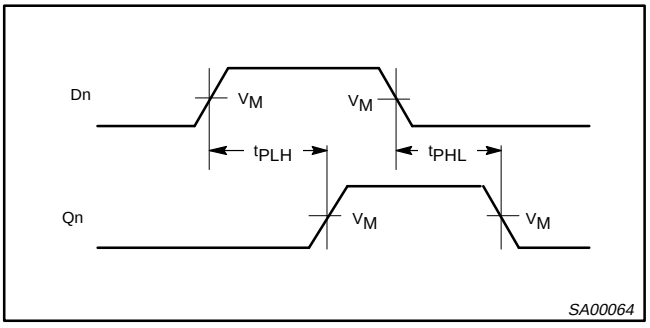
V_M = 1.5V, V_{IN} = GND to 3.0V



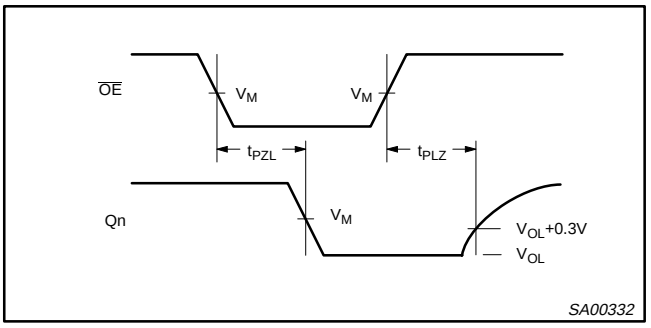
Waveform 1. Propagation Delay, Enable to Output, and Enable Pulse Width



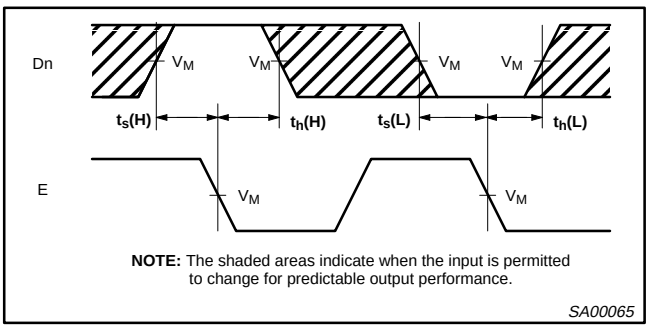
Waveform 4. 3-State Output Enable Time to High Level and Output Disable Time from High Level



Waveform 2. Propagation Delay for Data to Outputs



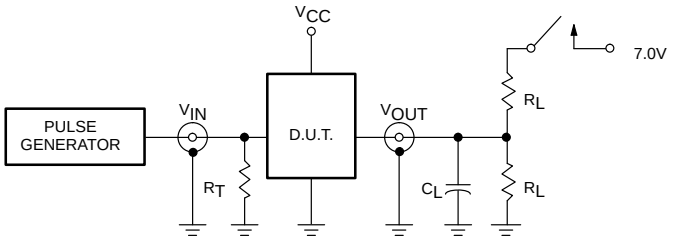
Waveform 5. 3-State Output Enable Time to Low Level and Output Disable Time from Low Level



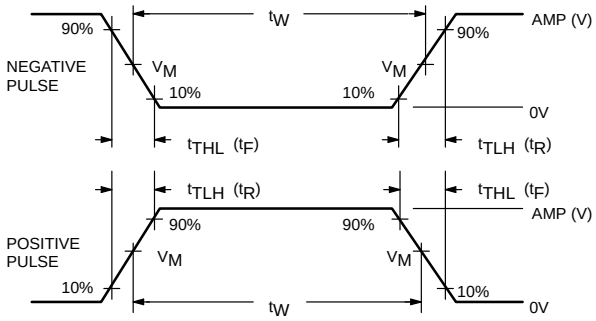
NOTE: The shaded areas indicate when the input is permitted to change for predictable output performance.

Waveform 3. Data Setup and Hold Times

TEST CIRCUIT AND WAVEFORM



Test Circuit for 3-State Outputs



V_M = 1.5V

Input Pulse Definition

SWITCH POSITION

TEST	SWITCH
t_{PLZ}	closed
t_{PZL}	closed
All other	open

DEFINITIONS

R_L = Load resistor; see AC CHARACTERISTICS for value.

C_L = Load capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.

R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.

FAMILY	INPUT PULSE REQUIREMENTS				
	Amplitude	Rep. Rate	t_W	t_R	t_F
74ABT	3.0V	1MHz	500ns	2.5ns	2.5ns

SA00012